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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Patent Application of
Seiichi FUKUDA

Serial No. 09/512,336

Filed: February 24, 2000

For: DRY ETCHING METHOD AND
METHOD OF MANUFACTURING
SEMICONDUCTOR APPARATUS

Group Art Unit: 1765

Examiner: K. Chen

TO 1700 MAIL ROOM

RECEIVED
OCT 15 2002

AMENDMENT AFTER FINAL UNDER 37 C.F.R § 1.116

BOX AF

Commissioner for Patents
Washington, DC 20231

Sir:

This is a complete and timely response to the final Office Action dated July 9, 2002. Please amend the application as follows.

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IN THE CLAIMS:

Please cancel claims 2 to 3, and 7 to 8. Please further amend claims 1 and 4 as shown in the attached Appendix to include the features of canceled claims 2 to 3, and 7 to 8, respectively. A clean version of the claims is presented below.

C. 1. (amended) A dry etching method comprising the step of:
~~dry-etching tungsten using only a single mixed gas~~

~~including a fluorine-containing gas that includes a compound~~